鼎德丰
DING DE FENG

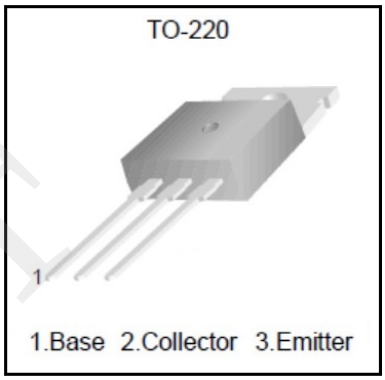
NPN Silicon Transistor

TIP41C

- **Complementary to：TIP42C**
- **Package：TO-220**

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV_{CBO}	100	V
Collector-emitter voltage	BV_{CEO}	100	V
Emitter-base voltage	BV_{EBO}	5	V
Collector current	I_{CM}	6	A
Collector Power Dissipation	P_C	2	W
	$P_C(T_C= 25°)$	65	
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃



Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=1mA，I_E=0	100			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=30mA，I_B=0	100			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA，I_C=0	5			V
collector-base cut-off current	I_{CBO}	V_{CB}=100V，I_E=0			400	μA
collector-emitter cut-off current	I_{CEO}	V_{CE}=60V，I_B=0			700	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=5V，I_C=0			1	mA
DC current gain	H_{FE1}	V_{CE}=4V，I_C=3A	15		75	
	H_{FE2}	V_{CE}=4V，I_C=0.3A	30			
collector-emitter saturation voltage	V_{CESAT}	I_C=6A，I_B=0.6A			1.5	V
Base-Emitter Saturation Voltage	$V_{BE(ON)}$	V_{CE}=4V，I_C=6A			2.0	V
Transition frequency	f_T	V_{CE}=10V，I_C=500mA	3			MH_Z